# Rectifier diodes schottky barrier

# PBYR2545CTF series

## **GENERAL DESCRIPTION**

Dual, low leakage, platinum barrier, schottky barrier rectifier diodes in a full pack, plastic envelope featuring low forward voltage drop and absence of stored charge. These devices can withstand reverse voltage transients and have guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

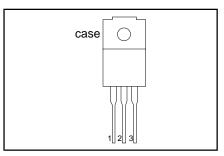
# **QUICK REFERENCE DATA**

| SYMBOL                            | PARAMETER   | MAX.            | MAX.            | MAX.            | UNIT   |
|-----------------------------------|---|-----------------|-----------------|-----------------|--------|
| V <sub>RRM</sub>                  | PBYR25-<br>Repetitive peak reverse<br>voltage                 | <b>35CTF</b> 35 | <b>40CTF</b> 40 | <b>45CTF</b> 45 | V      |
| V <sub>F</sub> I <sub>O(AV)</sub> | Forward voltage<br>Output current (both<br>diodes conducting) | 0.65<br>20      | 0.65<br>20      | 0.65<br>20      | V<br>A |

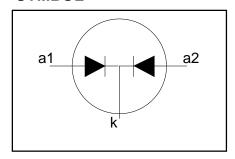
# **PINNING - SOT186**

| PIN | DESCRIPTION |  |
|-----|-------------|--|
| 1   | anode 1 (a) |  |
| 2   | cathode (k) |  |
| 3   | anode 2 (a) |  |
|     |             |  |
|     |             |  |

# **PIN CONFIGURATION**



# **SYMBOL**



# LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL   | PARAMETER  | CONDITIONS  | MIN.     | MAX.                         |                              | UNIT                         |                  |
|--|--|---|----------|------------------------------|------------------------------|------------------------------|------------------|
| V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | Repetitive peak reverse voltage<br>Crest working reverse voltage<br>Continuous reverse voltage | T <sub>hs</sub> ≤ 111 °C  | 1 1 1    | <b>-35</b><br>35<br>35<br>35 | <b>-40</b><br>40<br>40<br>40 | <b>-45</b><br>45<br>45<br>45 | <<<              |
| I <sub>O(AV)</sub>                                     | Output current (both diodes conducting)  | square wave; $\delta$ = 0.5; $T_{hs} \le 104 ^{\circ}\text{C}$  | -        |                              | 20                           |                              | A                |
| O(RMS)<br>I <sub>FRM</sub>                             | RMS forward current<br>Repetitive peak forward current<br>per diode                            | $t = 25 \mu s; \ \delta = 0.5;$<br>$T_{hs} \le 104 \ ^{\circ}C$   | -        |                              | 20<br>20                     |                              | A<br>A           |
| I <sub>FSM</sub>                                       | Non-repetitive peak forward current per diode  | t = 10 ms<br>t = 8.3 ms<br>sinusoidal; T <sub>j</sub> = 125 °C prior<br>to surge; with reapplied<br>V <sub>RWM(max)</sub> | -        |                              | 135<br>150                   |                              | A<br>A           |
| l <sup>2</sup> t                                       | I <sup>2</sup> t for fusing  | t = 10 ms   | -        |                              | 91                           |                              | A <sup>2</sup> s |
| I <sub>RRM</sub>                                       | Repetitive peak reverse current per diode.   | ,   | -        |                              | 1                            |                              | Α                |
| I <sub>RSM</sub>                                       | Non-repetitive peak reverse current per diode.   | $t_p = 100 \ \mu s$   | -        |                              | 1                            |                              | A                |
| $T_{stg}$  | Storage temperature Operating junction temperature   |   | -65<br>- |                              | 175<br>150                   |                              | °C               |

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# **ISOLATION**

 $T_{hs}$  = 25 °C unless otherwise specified

| SYMBOL            | PARAMETER   | CONDITIONS                      | MIN. | TYP. | MAX. | UNIT |
|-------------------|---|---------------------------------|------|------|------|------|
| V <sub>isol</sub> | Repetitive peak voltage from all three terminals to external heatsink | R.H. ≤ 65% ; clean and dustfree | -    | -    | 1500 | V    |
| C <sub>isol</sub> | Capacitance from T2 to external heatsink                              | f = 1 MHz                       | -    | 12   | -    | pF   |

# THERMAL RESISTANCES

| SYMBOL               | PARAMETER                              | CONDITIONS                              | MIN. | TYP. | MAX. | UNIT |
|----------------------|--|---|------|------|------|------|
| R <sub>th j-hs</sub> | Thermal resistance junction to         | per diode                               | -    | -    | 4.8  | K/W  |
| , ,                  | heatsink                               | both diodes<br>(with heatsink compound) | -    | -    | 4.0  | K/W  |
| R <sub>th j-a</sub>  | Thermal resistance junction to ambient | in free air.                            | -    | 55   | -    | K/W  |

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

| SYMBOL         | PARAMETER                   | CONDITIONS   | MIN. | TYP.      | MAX. | UNIT     |
|----------------|-----------------------------|--|------|-----------|------|----------|
| V <sub>F</sub> | Forward voltage (per diode) | $I_F = 20 \text{ A}; T_i = 125^{\circ}\text{C}$  | -    | 0.58      | 0.65 | V        |
|                |                             | $I_{\rm F} = 20  \text{A}$   | -    | 0.63      | 0.68 | V        |
| I <sub>R</sub> | Reverse current (per diode) | $\dot{V}_{R} = V_{RWM}$  | -    | 100       | 200  | μA       |
|                | Junction capacitance (per   | $V_R = V_{RWM}$ ; $T_j = 125  ^{\circ}C$<br>$f = 1MHz$ ; $V_R = 5V$ ; $T_i = 25  ^{\circ}C$ to | -    | 12<br>800 | 40   | mA<br>pF |
| C <sub>d</sub> | diode)                      | 125 °C   | •    | 000       | •    | ρΓ       |

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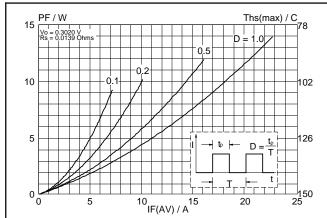


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$ .

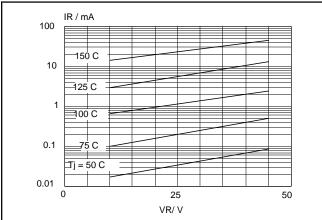


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

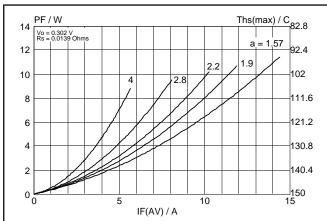


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = f form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

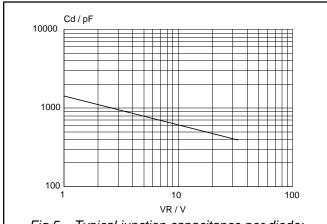


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125 °C.

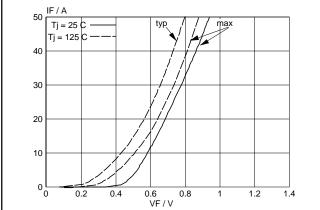


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

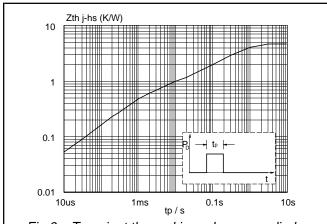
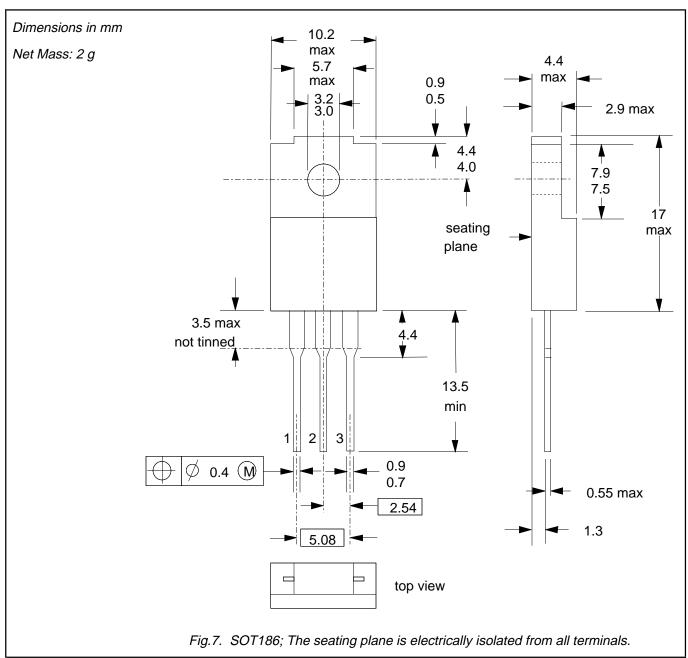


Fig.6. Transient thermal impedance per diode;  $Z_{th j ext{-}hs} = f(t_p)$ .

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# **MECHANICAL DATA**



- Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
   Epoxy meets UL94 V0 at 1/8".

| Rectifier | diodes  |
|-----------|---------|
| schottky  | barrier |

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## **DEFINITIONS**

| Data sheet status   |   |  |  |  |  |
|---|---|--|--|--|--|
| Objective specification   | This data sheet contains target or goal specifications for product development. |  |  |  |  |
| Preliminary specification This data sheet contains preliminary data; supplementary data may be published late |   |  |  |  |  |
| Product specification This data sheet contains final product specifications.                                  |   |  |  |  |  |
|   |   |  |  |  |  |

## Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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